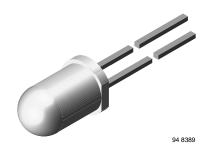


Vishay Semiconductors

High Speed Infrared Emitting Diode, 850 nm, GaAIAs Double Hetero



FEATURES

- · Package type: leaded
- Package form: T-1³/₄
- Dimensions (in mm): Ø 5
- Peak wavelength: $\lambda_p = 850 \text{ nm}$
- · High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\phi = \pm 10^{\circ}$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: $f_c = 18 \text{ MHz}$
- · Good spectral matching with CMOS cameras
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission

DESCRIPTION

TSHG6200 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

PRODUCT SUMMARY				
COMPONENT	l _e (mW/sr)	φ (deg)	λ _p (nm)	t _r (ns)
TSHG6200	180	± 10	850	20

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TSHG6200	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾	

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current		I _F	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	1	А	
Power dissipation		Pv	180	mW	
Junction temperature		Тj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 85	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	$t \leq$ 5 s, 2 mm from case	T _{sd}	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R _{thJA}	230	K/W	

Note

 T_{amb} = 25 °C, unless otherwise specified





TSHG6200

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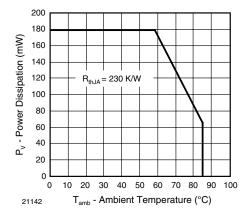


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

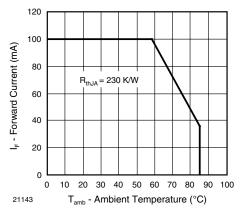


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F		1.5	1.8	V
	I _F = 1 A, t _p = 100 μs	V _F		2.3		V
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μΑ
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	Cj		125		pF
Radiant intensity	I _F = 100 mA, t _p = 20 ms	le	120	180	360	mW/sr
	I _F = 1 A, t _p = 100 μs	l _e		1800		mW/sr
Radiant power	I _F = 100 mA, t _p = 20 ms	φ _e		50		mW
Temperature coefficient of ϕ_{e}	I _F = 100 mA	TKφe		- 0.35		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	I _F = 100 mA	λρ		850		nm
Spectral bandwidth	I _F = 100 mA	Δλ		40		nm
Temperature coefficient of λ_p	I _F = 100 mA	ΤΚλρ		0.25		nm/K
Rise time	I _F = 100 mA	t _r		20		ns
Fall time	I _F = 100 mA	t _f		13		ns
Cut-off frequency	$I_{DC} = 70 \text{ mA}, I_{AC} = 30 \text{ mA pp}$	f _c		18		MHz
Virtual source diameter		d		3.7		mm

Note

 $T_{amb} = 25$ °C, unless otherwise specified



High Speed Infrared Emitting Diode, Vishay Semiconductors 850 nm, GaAlAs Double Hetero

TSHG6200

BASIC CHARACTERISTICS

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

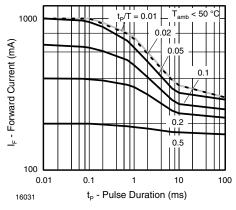


Fig. 3 - Pulse Forward Current vs. Pulse Duration

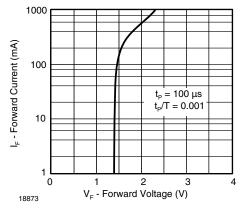


Fig. 4 - Forward Current vs. Forward Voltage

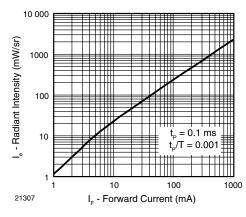
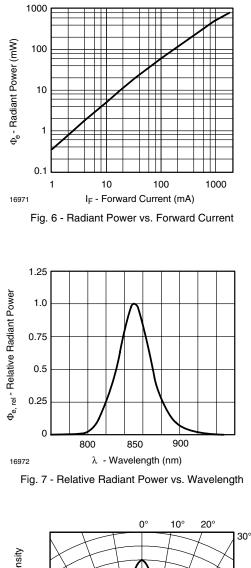


Fig. 5 - Radiant Intensity vs. Forward Current



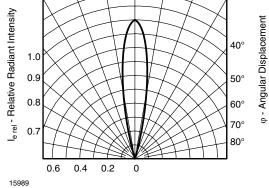
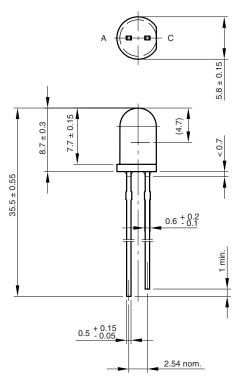


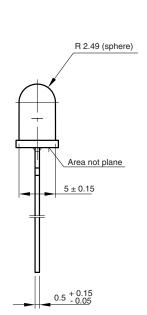
Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

Vishay Semiconductors High Speed Infrared Emitting Diode, 850 nm, GaAlAs Double Hetero



PACKAGE DIMENSIONS in millimeters







according to DIN specifications

6.544-5259.02-4 Issue: 8; 19.05.09 95 10917



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